



## 650V 16A 0.48Ω N-ch Power MOSFET

# **Description**

DT2 MOS is DIN-TEK 2<sup>nd</sup> generation VDMOS family that is dramatic reduction in on-resistance and ultra-low gate charge for applications requiring high power density and high efficiency. And it is very robust and RoHS compliant.

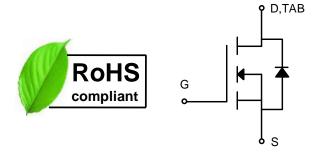
## **Features**

- Typ.R<sub>DS(on)</sub>=0.48 $\Omega$ @V<sub>GS</sub>=10V
- 100% avalanche tested
- RoHS Compliant

# **Applications**

- SMPS
- Charger
- DC-DC





## **Absolute Maximum Ratings** (Tc=25℃)

Parameter	Symbol	DTP16N65	DTP16N65F	Unit
Drain-source voltage	V <sub>DSS</sub>	650		V
Gate-source voltage	V <sub>G</sub> S	<u>±</u>	±30	V
Continuous drain current	ID		16	А
Pulsed drain current <sup>1</sup>	I <sub>DM</sub>		А	
Avalanche energy, single pulse <sup>2</sup>	Eas	9	mJ	
Power dissipation	P <sub>D</sub>	156	62.5	W
Derate above 25°C		1.3 0.5		W/°C
Operating junction temperature	Tj	-55~150		°C
Storage temperature	T <sub>stg</sub>	-55~150		°C
Continuous diode forward current	Is	16		А
Diode pulse current <sup>1</sup>	I <sub>Spulse</sub>	64		

## **Thermal Characteristic**

Thermal resistance, junction-to-case	$R_{ heta JC}$	0.8	2	°C/W
Thermal resistance, junction-to-ambient	$R_{\theta JA}$	30	62.5	°C/W



# DTP16N65/DTP16N65F

Min

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Max

<b>Flectrical</b>	<b>Characteristics</b>	of MOSEET
LICCUICAL	CHALACIEL ISLICS	ULWUSELI

Electrical Characteristics of i	VIOSFEI			Min.	Тур.	Max.	
Drain-source break down voltage	BV <sub>DSS</sub>	I <sub>D</sub> =250µA, V <sub>GS</sub> =0V	Tc=25°C	650	-	-	V
Gate threshold voltage	$V_{GS(th)}$	I <sub>D</sub> =250µA, V <sub>DS</sub> =V <sub>GS</sub>	TJ=25°C	2.0	-	4.0	V
Drain-source leakage current	I <sub>DSS</sub>	V <sub>DS</sub> =650V, V <sub>GS</sub> =0V	TJ=25°C	-	-	1	μΑ
		V <sub>DS</sub> =520V, V <sub>GS</sub> =0V	TJ=125°C	-	-	100	μΑ
Gate-source leakage current,forward	I <sub>GSSF</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =30V	TJ=25°C	-	-	100	nA
Gate-source leakage current,reverse	Igssr	V <sub>DS</sub> =0V, V <sub>GS</sub> =-30V	TJ=25°C	-	-	-100	nA
Drain-source on-state resistance <sup>3</sup>	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =8A	TJ=25°C	-	0.48	0.58	Ω

## **Dynamic Characteristics of MOSFET** (Tc=25℃)

			IVIII I.	τyp.	iviax.	
Input capacitance	Ciss		-	2740	-	pF
Output capacitance	Coss	f=1MHz, V <sub>DS</sub> =25V, V <sub>GS</sub> =0V	-	215	-	pF
Reverse transfer capacitance	C <sub>rss</sub>		-	15	-	pF
Gate to source charge	Qgs	V <sub>DD</sub> =300V	-	16	-	nC
Gate to drain charge	$Q_{gd}$	I <sub>D</sub> =16A	-	16	-	nC
Total gate charge	Qg	V <sub>GS</sub> = 0 to10V	-	61	-	nC

## Switching Characteristics of MOSFET $(T_C=25^{\circ}C)$

Switching Characteristics of MOSPET (16=25 C)			Min.	Тур.	Max.	
Turn-on delay time	t <sub>d on</sub>		-	35	-	ns
Rise time	tr	V <sub>DS</sub> =320V, I <sub>D</sub> =16A,	-	50	-	ns
Turn-off delay time	t <sub>d off</sub>	$R_G=25\Omega$ , $V_{GS}=0$ to $10V$	-	160	-	ns
Fall time	t <sub>f</sub>		-	65	-	ns

## Characteristics of Body Diode (T<sub>C</sub>=25℃)

			IVIII.	тур.	wax.	
Forward voltage	V <sub>SD</sub>	I <sub>SD</sub> =16A, V <sub>GS</sub> =0V	ı	-	1.4	V
Reverse recovery time	t <sub>rr</sub>	V <sub>DS</sub> =320V, I <sub>S</sub> =16A, V <sub>GS</sub> =10V — di/dt=100A/µs	ı	574	-	ns
Reverse recovery current	Irr		-	20	-	Α
Recovery charge	Qrr	αι/αι=100/ν μδ	-	5.7	-	μC

#### Notes:

- 1. Repetitive rating, pulse width limited by junction temperature  $T_{J(MAX)}$  =150°C.
- 2. The EAS data shows Max. rating . The test condition is  $V_{DD}$  =50V,  $V_{GS}$  =10V, L=10mH, IAS =14A,Tc=25°C.
- 3. The data tested by pulsed , pulse width  $\leq 300 \mu s$  , duty cycle  $\leq 2\%.$

#### TYPICAL CHARACTERISTICS

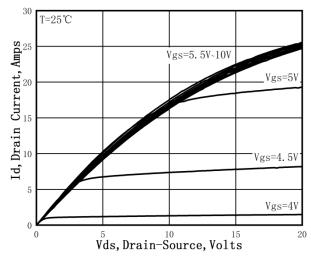


Figure 1.On-Region Characteristics

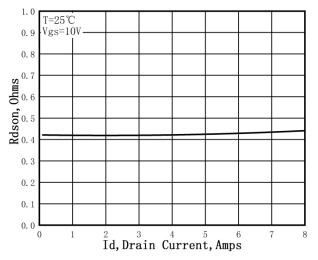


Figure 3. Static Drain-Source On Resistance

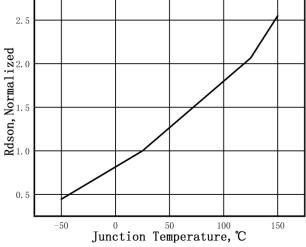


Figure 5. Normalized R<sub>DS(on)</sub> vs.Temperature

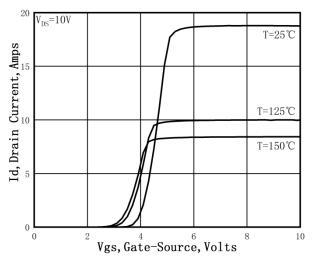


Figure 2. Transfer Characteristics

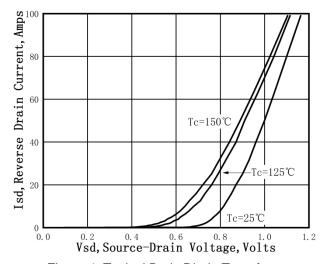


Figure 4. Typical Body Diode Transfer Characteristics

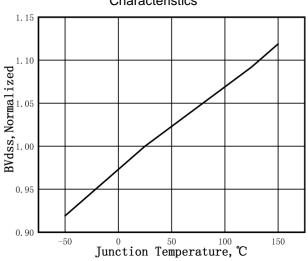
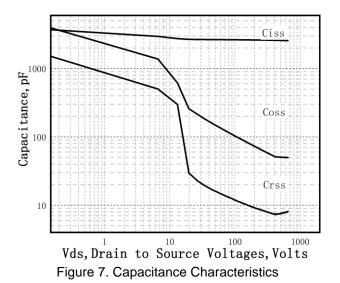


Figure 6. Normalized BV<sub>DSS</sub> vs.Temperature



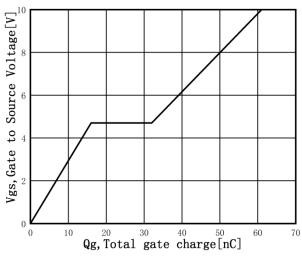
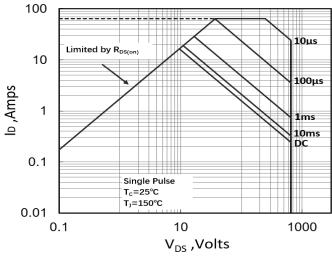


Figure 8. Gate Charge Characteristics



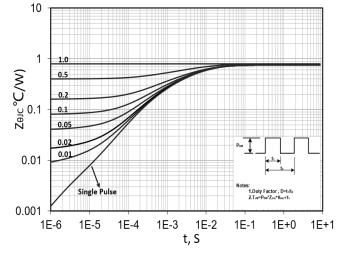
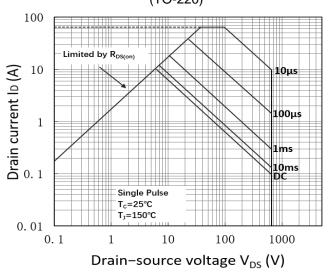


Figure 9. Maximum Safe Operating Area (TO-220)

Figure 10. Transient Thermal Response Curve (TO-220)



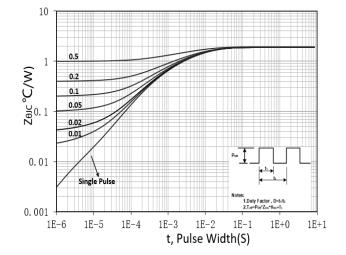
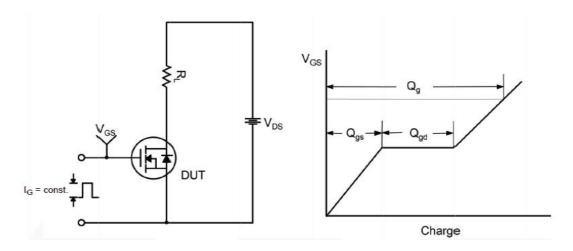


Figure 11. Maximum Safe Operating Area (TO-220F)

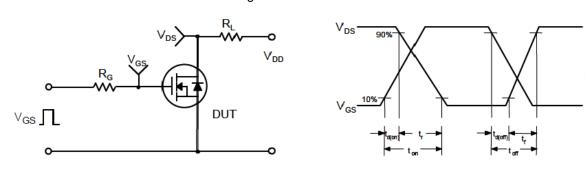
Figure 12. Transient Thermal Response Curve (TO-220F)

## **Test Circuit**

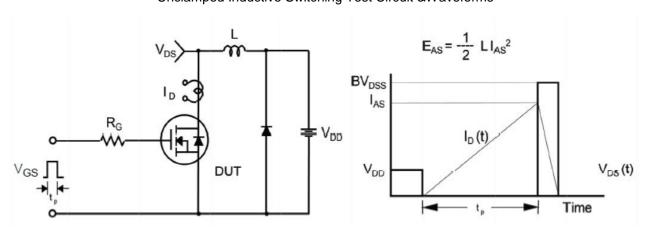
## Gate Charge Test Circuit &Waveform



## Switching Test Circuit &Waveforms

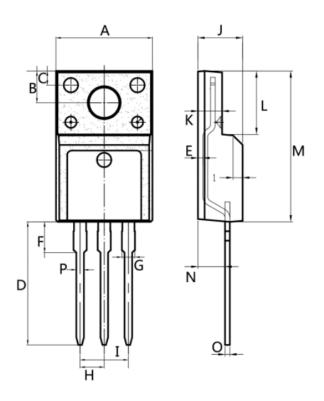


## Unclamped Inductive Switching Test Circuit &Waveforms





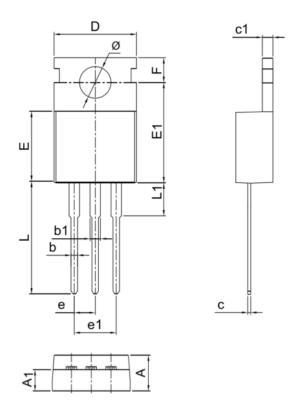
## **Mechanical Dimensions for TO-220F**



#### **COMMON DIMENSIONS**

SYMBOL	M	М
STIVIBUL	MIN	MAX
Α	9.95	10.36
В	2.95	3.55
С	1.25	1.6
D	12.64	13.5
Е	0.40	0.60
F	2.80	3.80
G	1.14	1.58
Н	2.44	2.64
1	4.88	5.26
J	4.50	4.90
K	2.34	2.80
L	6.48	6.90
M	15.40	16.07
N	2.66	3.50
0	0.40	0.64
Р	0.70	0.94

## **Mechanical Dimensions for TO-220**



## **COMMON DIMENSIONS**

CVMDOL	M	М
SYMBOL	MIN	MAX
Α	4.30	4.70
A1	2.30	2.82
b	0.70	0.94
b1	1.17	1.41
С	0.30	0.64
c1	1.17	1.44
D	9.70	10.20
Е	8.50	9.30
E1	12.00	12.50
е	2.44	2.64
e1	4.88	5.26
F	2.60	2.94
L	13.00	14.00
L1	3.385	4.20
Ø	3.74	3.95





# **Ordering Information**

Part	Package	Packing method
DTP16N65F	TO-220F	Tube
DTP16N65	TO-220	Tube





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